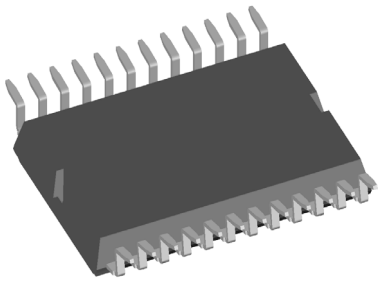
Three phase full Bridge

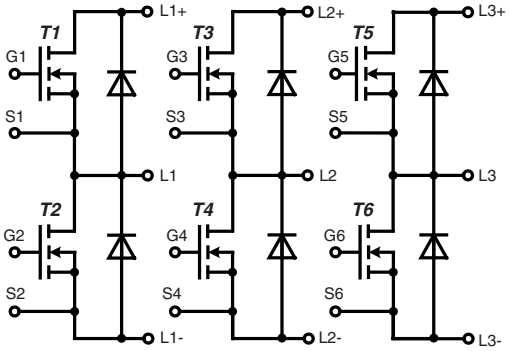
with Trench MOSFETs
in DCB isolated high current package

V_{DSS} = 75 V
I_{D25} = 255 A
$R_{DSon\ typ.}$ = 1.1 mΩ

Part number
MTI200WX75GD



Surface Mount Device



Features / Advantages:

- MOSFETs in trench technology:
  - low R_{DSon}
  - optimized intrinsic reverse diode
- package:
  - high level of integration
  - high current capability
  - aux. terminals for MOSFET gate control
  - terminals for soldering or welding connections
  - isolated DCB ceramic base plate with optimized heat transfer
- Space and weight savings
- High current capability

Applications:

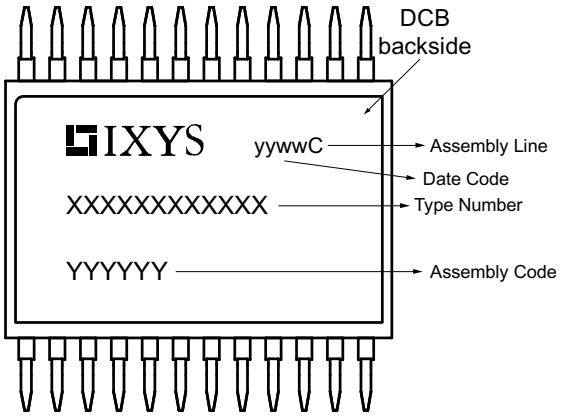
AC drives
- in automobiles
  - electric power steering
  - starter generator
- in industrial vehicles
  - propulsion drives
  - fork lift drives
- Battery supplied equipment
- DC-DC converter

Package: ISOPLUS-DIL®

- High level of integration
- RoHS compliant
- Terminals for soldering or welding connections
- Space and weight savings
- High reliability
- Low thermal impedance

MOSFETs				Ratings			
Symbol	**Definitions**	**Conditions**		**min.**	**typ.**	**max.**	**Unit**
V_{DSS}	*drain source breakdown voltage*		T_{VJ} = 25°C to 150°C			75	V
V_{GS}	*max. DC gate source voltage*					±15	V
V_{GSM}	*max. transient gate source voltage*					±20	V
I_{D25}	*continuous drain current*		T_C = 25°C			255	A
I_{D90}	*(die capability)*		T_C = 90°C			190	A
$R_{DS(on)}$ [1]	*static drain source on resistance*	on chip level at	T_{VJ} = 25°C		1.1	1.3	mΩ
		I_D = 100 A; V_{GS} = 10 V	T_{VJ} = 125°C		1.8		mΩ
$V_{GS(th)}$	*gate threshold voltage*	I_D = 275 µA; V_{DS} = V_{GS}	T_{VJ} = 25°C	2.3	3.1	3.8	V
I_{DSS}	*drain source leakage current*	V_{DS} = V_{DSS}; V_{GS} = 0 V	T_{VJ} = 25°C			1	µA
			T_{VJ} = 125°C		10	100	µA
I_{GSS}	*gate source leakage current*	V_{GS} = ±20 V; V_{DS} = 0 V				500	nA
R_G	*gate resistance*	on chip			2.7		Ω
C_{iss}	*input capacitance*	V_{GS} = 0 V; V_{DS} = 38 V; f = 1 Mhz			10.8	14.4	nF
C_{oss}	*output capacitance*				2.42	3.22	nF
C_{rss}	*reverse transfer capacitance*				110	-	pF
Q_g	*total gate charge*	V_{GS} = 10 V; V_{DS} = 38 V; I_D = 100 A			155		nC
Q_{gs}	*gate source charge*				53		nC
Q_{gd}	*gate drain (Miller) charge*				32		nC
$t_{d(on)}$	*turn-on delay time*	inductive load	T_{VJ} = 125°C		145		ns
t_r	*current rise time*	V_{GS} = 10 V; V_{DS} = 30 V			70		ns
$t_{d(off)}$	*turn-off delay time*	I_D = 100 A; R_G = 27 Ω			520		ns
t_f	*current fall time*				55		ns
E_{on}	*turn-on energy per pulse*				80		µJ
E_{off}	*turn-off energy per pulse*				350		µJ
$E_{rec(off)}$	*turn-off reverse recovery losses*				8		µJ
R_{thJC}	*thermal resistance junction to case*					0.85	K/W
R_{thJH}	*thermal resistance junction to heatsink*	with heat transfer paste (IXYS test setup)			1.1	1.4	K/W
		[1] V_{DS} = I_D·($R_{DS(on)}$ + 2·$R_{Pin\ to\ Chip}$)					
Source-Drain Diode							
I_{F25}	*forward current (body diode)*	V_{GS} = 0 V	T_C = 25°C			175	A
I_{F90}			T_C = 90°C			100	A
V_{SD}	*source drain voltage*	I_F = 100 A; V_{GS} = 0 V	T_{VJ} = 25°C		0.9	1.2	V
Q_{RM}	*reverse recovery charge*	V_R = 30 V; I_F = 100 A	T_{VJ} = 125°C		730		nC
I_{RM}	*max. reverse recovery current*	R_G = 27 Ω			27		A
t_{rr}	*reverse recovery time*				42		ns

Package ISOPLUS-DIL®				Ratings			
Symbol	**Definitions**	**Conditions**		**min.**	**typ.**	**max.**	**Unit**
I_{RMS}	*RMS current*	per pin in main current paths (L1+...L3+, L1-...L3-, L1...L3) may be additionally limited by external connections (PCB tracks) 2 pins for output L1, L2, L3				75	A
T_{stg}	*storage temperature*			-55		125	°C
T_{op}	*operation temperature*			-55		150	°C
T_{VJ}	*virtual junction temperature*			-55		175	°C
Weight					13		g
F_C	*mounting force with clip*			50		250	N
V_{ISOL}	*isolation voltage*	t = 1 second	50/60 Hz, RMS, $I_{ISOL} \leq 1$ mA	1200			V
		t = 1 minute		1000			V
$R_{pin\text{-}chip}$	*resistance terminal to chip*	$V_{DS} = I_D \cdot (R_{DS(on)} + 2 \cdot R_{pin\ to\ chip})$			0.5		mΩ
C_P	*coupling capacity*	between shorted pins and back side metallization			160		pF

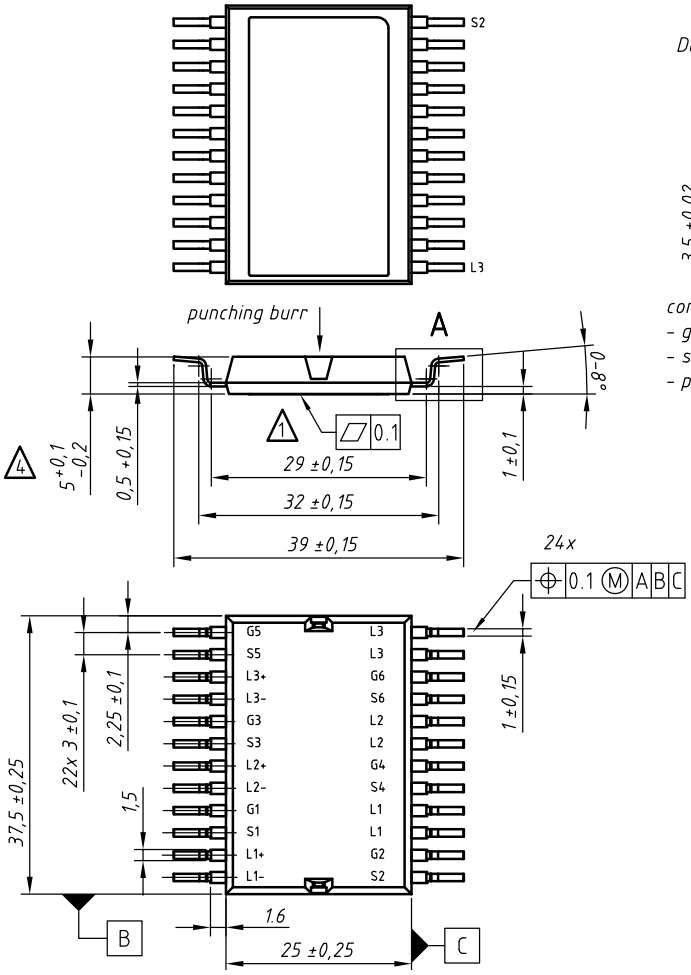


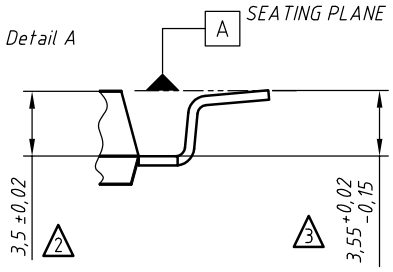
Part number

M = MOSFET
T = Trench
I = Infineon Trench
200 = Current Rating [A]
WX = 6-Pack with separated phase legs
75 = Reverse Voltage [V]
GD = ISOPLUS-DIL

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MTI200WX75GD-SMD	MTI200WX75GD	Tube	13	516955

Outlines ISOPLUS-DIL®





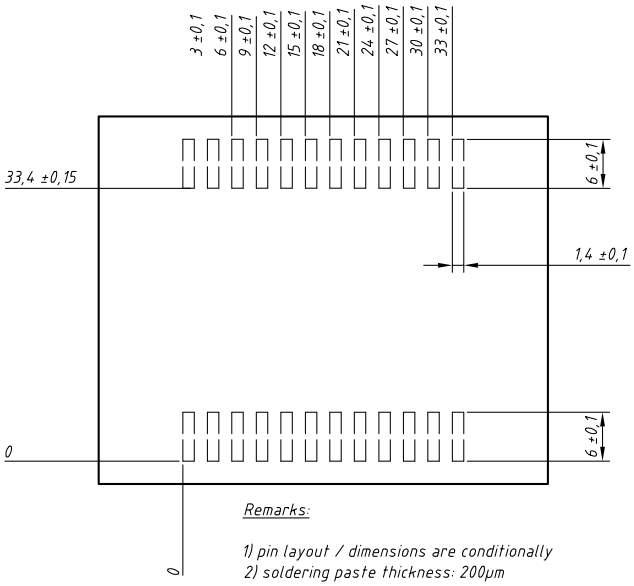
contact pin:
- galv. tin plating, per pin side: Sn 10...25 µm, undercoating Ni 0,2...1 µm
- stamping edges may be free of tin
- puching burr: ≤ 0,05mm

1 Convex bow of substrate, typ. 10-40 µm longitudinal and 5-15 µm transversal

2 Distance between pin and case bottom side.

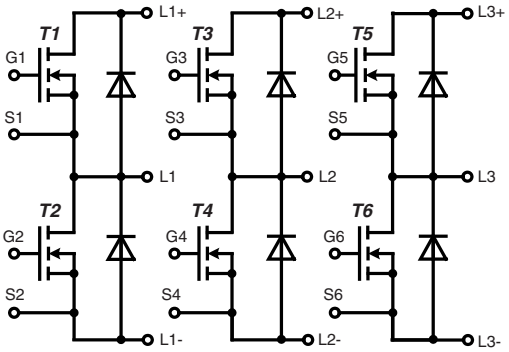
3 Distance between pin and contact surface.

4 Distance between parallel planes aligned to top and bottom sides of the package



Remarks:

1) pin layout / dimensions are conditionally
2) soldering paste thickness: 200µm



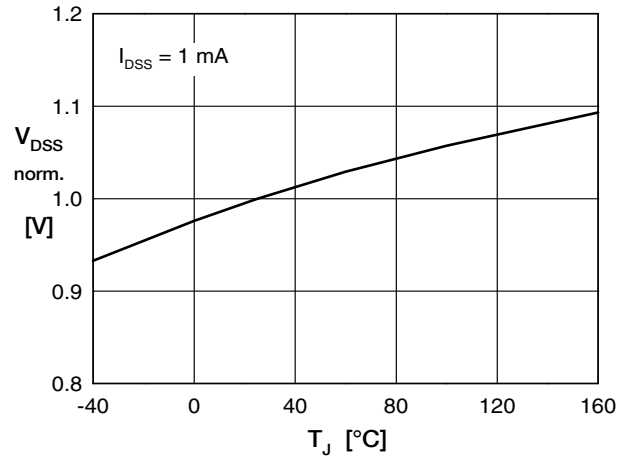


Fig.1 Drain source breakdown voltage V_{DSS} vs. junction temperature T_{VJ}

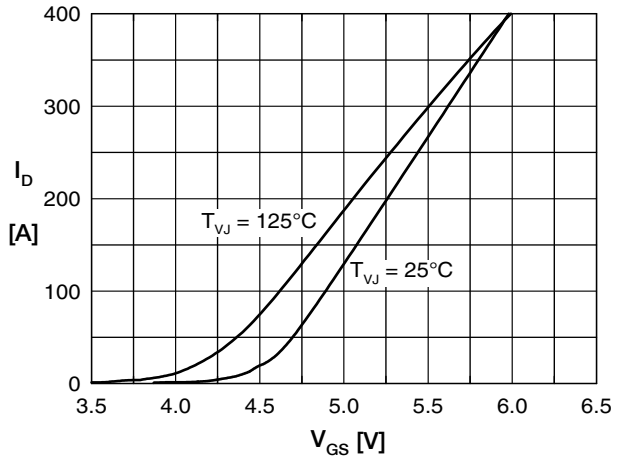


Fig. 2 Typ. transfer characteristics

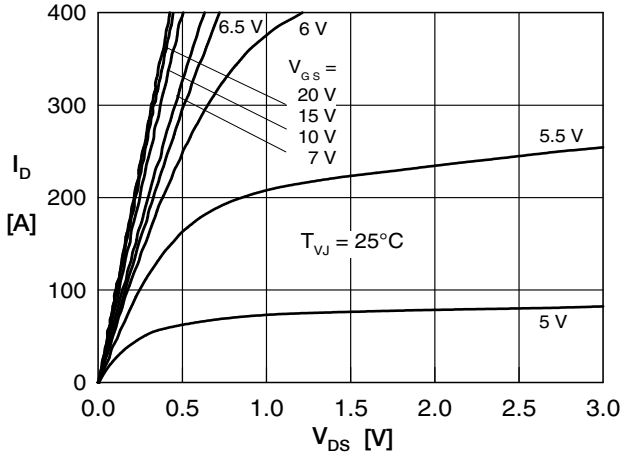


Fig. 3 Typ. output characteristics on die level

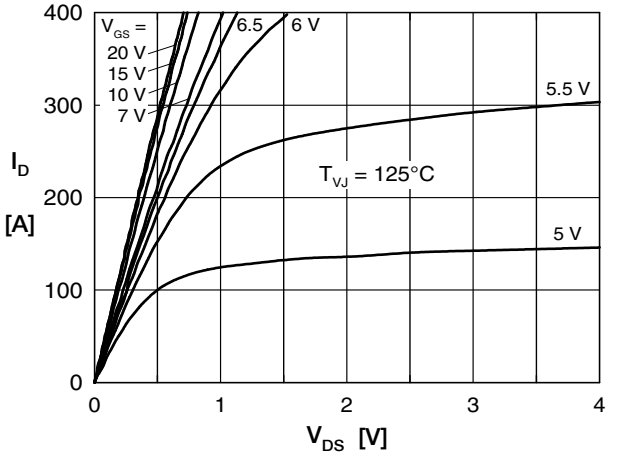


Fig. 4 Typ. output characteristics on die level

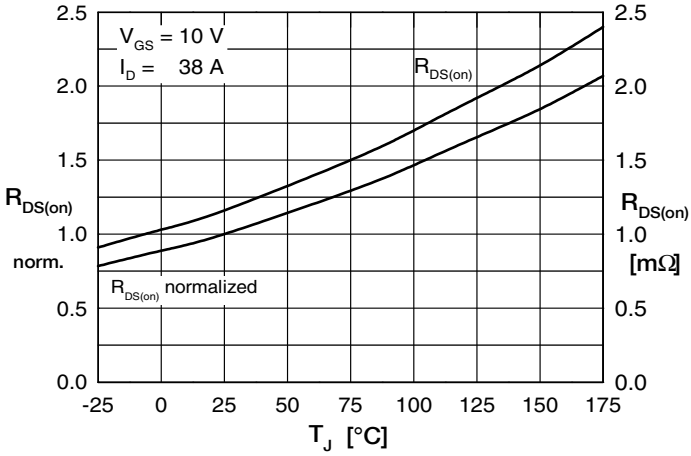


Fig.5 Drain source on-state resistance $R_{DS(on)}$ vs. junction temperature T_{VJ}, on die level

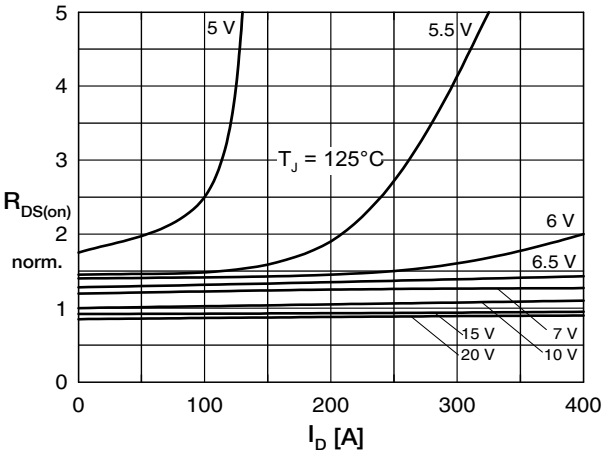


Fig. 6 Drain source on-state resistance $R_{DS(on)}$ versus I_D, on die level

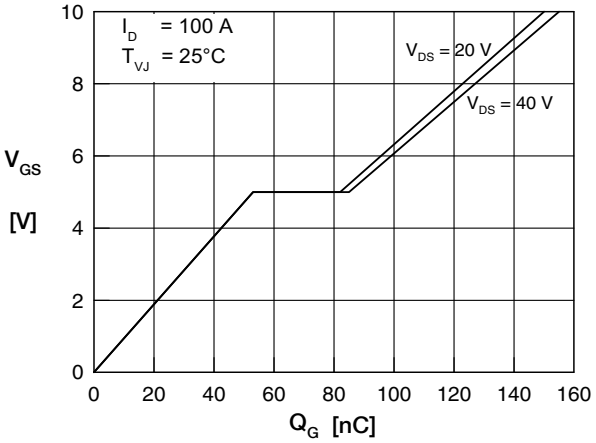


Fig.7 Typical turn on gate charge

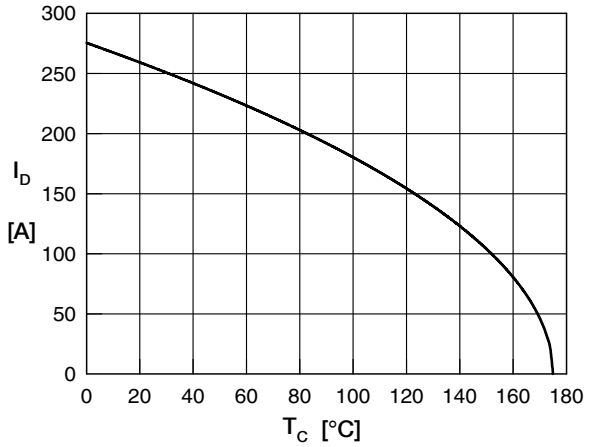


Fig. 8 Drain current I_D vs. case temperature T_C (Chip capability)

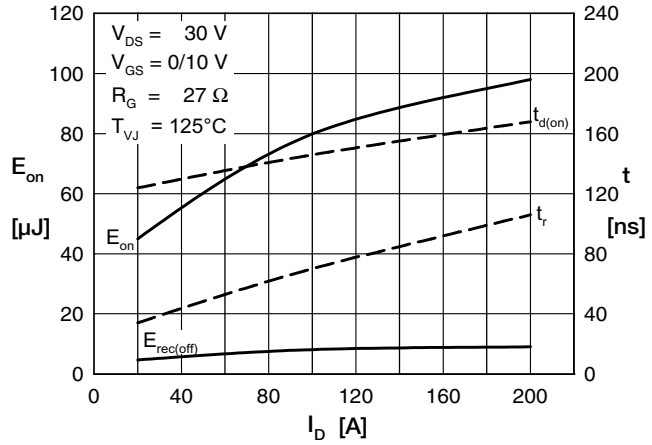


Fig. 9 Typ. turn-on energy and switching times versus drain current, inductive switching

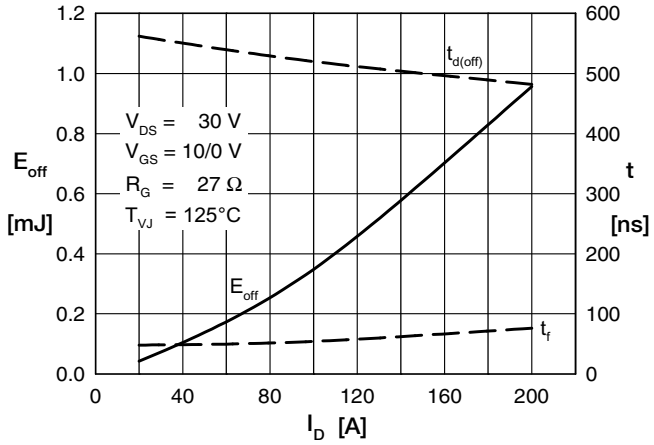


Fig. 10 Typ. turn-off energy and switching times versus drain-current, inductive switching

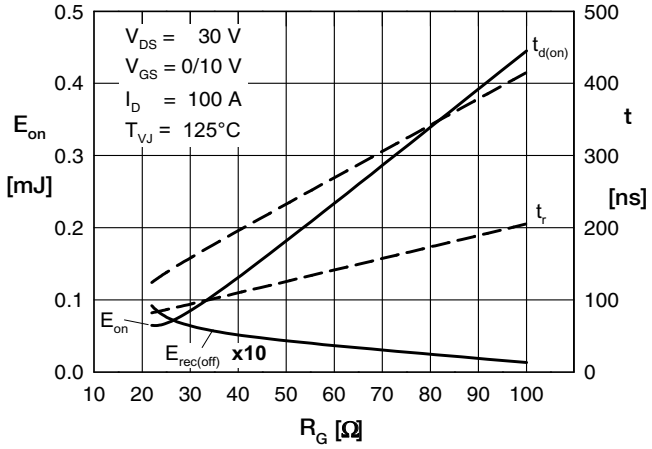


Fig. 11 Typ. turn-on energy and switching times versus gate resistor, inductive switching

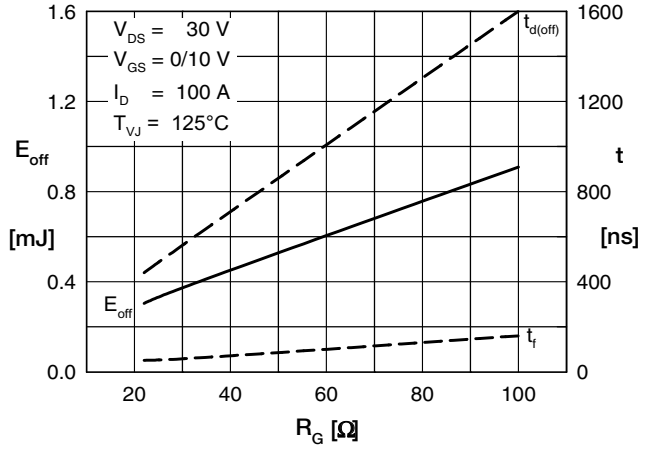


Fig. 12 Typ. turn-off energy and switching times versus gate resistor, inductive switching